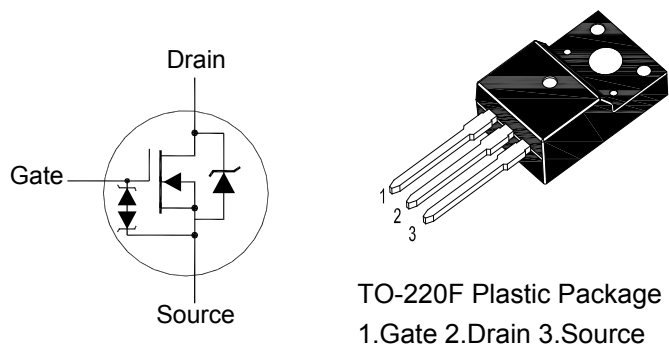


SFTN2580

N-Channel Enhancement Mode Power MOSFET

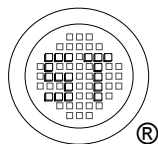


Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current	I_D	$T_C = 25^{\circ}C$ 19.5	A
		$T_C = 100^{\circ}C$ 12.3	
Peak Drain Current	I_{DM}	78	A
Power Dissipation	P_{tot}	40	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Maximum Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.1	$^{\circ}C/W$
Maximum Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^{\circ}C/W$

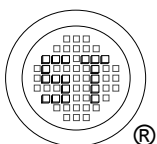


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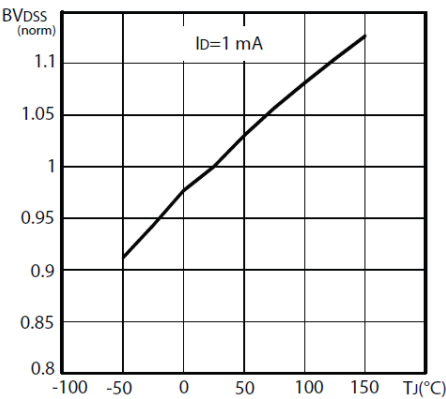
Characteristics at $T_C = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at $I_D = 1\text{ mA}$	BV_{DSS}	800	-	-	V
Drain-Source Leakage Current at $V_{DS} = 800\text{ V}$ at $V_{DS} = 800\text{ V}$, $T_C = 125^\circ\text{C}$	I_{DSS}	- -	- -	1 50	μA
Gate Leakage Current at $V_{GS} = \pm 20\text{ V}$	I_{GSS}	-	-	± 10	μA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	$V_{GS(th)}$	3	-	5	V
Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$	$R_{DS(on)}$	-	-	0.26	Ω
Diode Forward Voltage at $I_S = 19.5\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	-	-	1.5	V
Maximun Body-Diode Continuous Current	I_S	-	-	19.5	A
Input Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	1600	-	pF
Output Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	130	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	2	-	pF
Turn-On Delay Time at $I_D = 10\text{ A}$, $V_{DD} = 400\text{ V}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$	$t_{d(on)}$	-	25	-	ns
Turn-On Rise Time at $I_D = 10\text{ A}$, $V_{DD} = 400\text{ V}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$	t_r	-	13	-	ns
Turn-Off Delay Time at $I_D = 10\text{ A}$, $V_{DD} = 400\text{ V}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$	$t_{d(off)}$	-	60	-	ns
Turn-Off Fall Time at $I_D = 10\text{ A}$, $V_{DD} = 400\text{ V}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$	t_f	-	15	-	ns

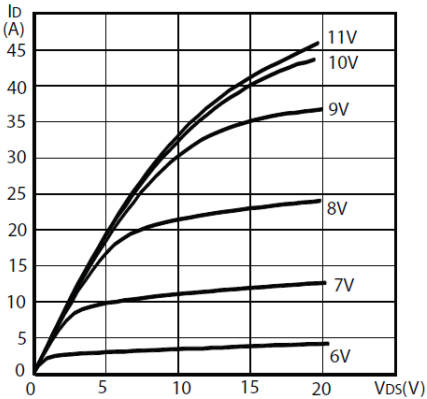


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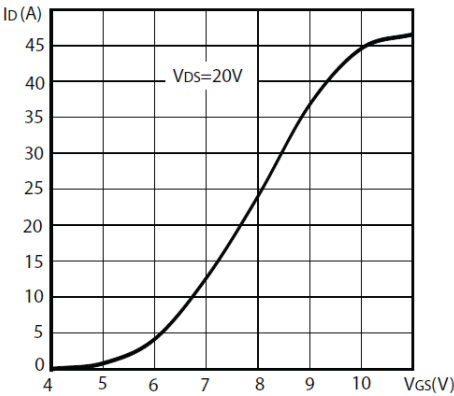




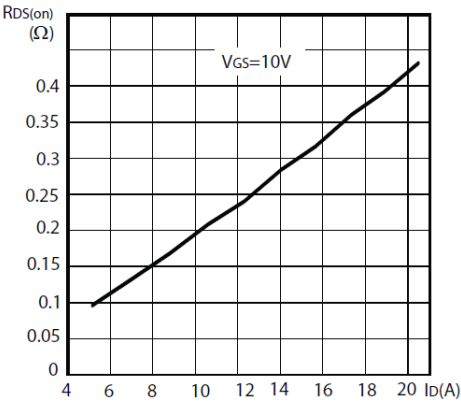
Normalized BV_{DSS} vs temperature



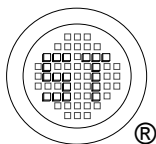
Output characteristics



Transfer characteristics



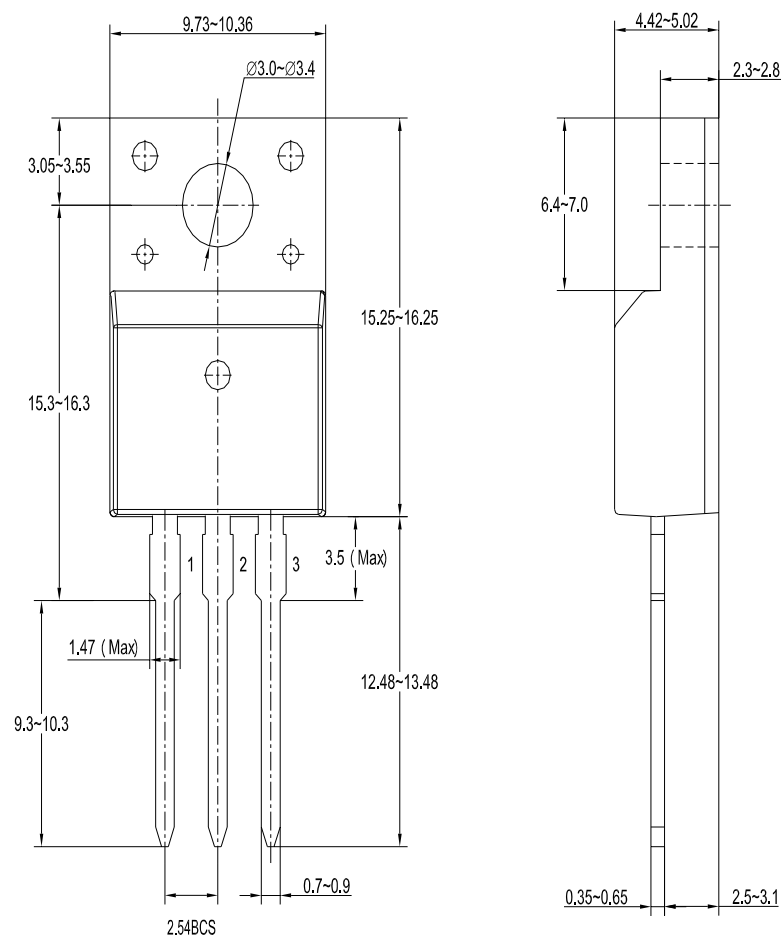
Static drain-source on-resistance



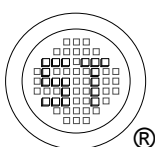
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TO-220F Package Outline



Dimensions in millimeters



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